

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-10 (Canceled).

11. (Previously Presented) A method for manufacturing a semiconductor chip, comprising the steps of:

providing a semiconductor wafer which includes a first layer having at least two partial layers, the first partial layer being disposed on the second partial layer, the two partial layers having a first conductivity type, the first partial layer having a first dopant concentration, the second partial layer having a second dopant concentration, and the second dopant concentration being less than the first dopant concentration;

introducing trenches into the first partial layer, which trenches extend through the first partial layer into the second partial layer;

introducing dopants of a second conductivity type into the top surface of the wafer to change the conductivity type of a section of the first partial layer and a section of the second partial layer, whereby a second layer is formed; and

depositing metallic coatings on the top surface and the bottom surface of the wafer; and

separating the wafer along the trenches into individual chips, such that each chip has at least one trench in its interior.

12. (Previously Presented) The method according to claim 11, further comprising the step of

introducing the trenches by sawing.

13. (Previously Presented) The method according to claim 11, further comprising the step of introducing the trenches by etching.